

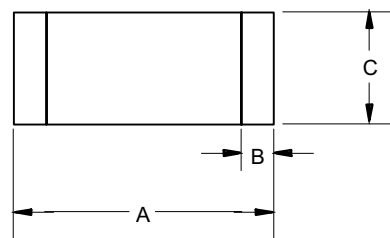


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LLDB3

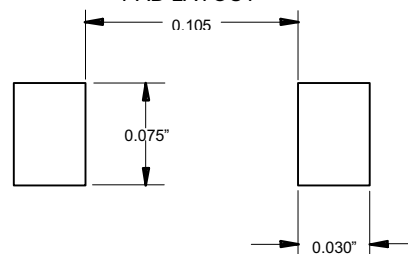
SILICON
BIDIRECTIONAL
DIAC

MiniMELF



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.130	.146	3.30	3.70	
B	.008	.016	.20	.40	
C	.055	.059	1.40	1.50	Ø

SUGGESTED SOLDER
PAD LAYOUT



Features

- Breakover Voltage: 32V
- Breakover Voltage Range: 28V to 36V
- Lead Free Finish/RoHS Compliant(Note 3) ("P" Suffix designates RoHS Compliant. See ordering information)
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1

Maximum Ratings

- Operating Junction Temperature: -40°C to +125°C
- Storage Temperature: -40°C to +125°C

Electrical Characteristics @ 25°C Unless Otherwise Specified

Power dissipation on Printed Circuit(I=10mm)	P_C	150mW	$T_A=50^{\circ}\text{C}$
Repetitive Peak on-state Current	I_{TRM}	2.0A	$t_p=20\mu\text{s}, f=120\text{Hz}$
Breakover Voltage	V_{BO}	Min Typ Max 28 32 36V	$C=22\text{nF}(\text{Note } 2)$
Breakover Voltage Symmetry	$ +V_{BO} $	$\pm 3\text{V}$	$C=22\text{nF}(\text{Note } 2)$
Output Voltage(Note 1)	$V_{o(\min)}$	5V	
Breakover Current(Note 1)	$I_{BO(\max)}$	50uA	$C=22\text{nF}$
Rise Time(Note 1)	T_r	2.0us	
Leakage Current(Note 1)	$I_{B(\max)}$	10uA	$V_B=0.5V_{BO(\max)}$

NOTES:1.Electrical characteristics applicable in both forward and reverse directions.

2.Connected in parallel with the devices.

3.Lead in Glass Exemption Applied, see EU Directive Annex 5.

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Fig. 1: Relative variation of VBO versus junction temperature (typical values)

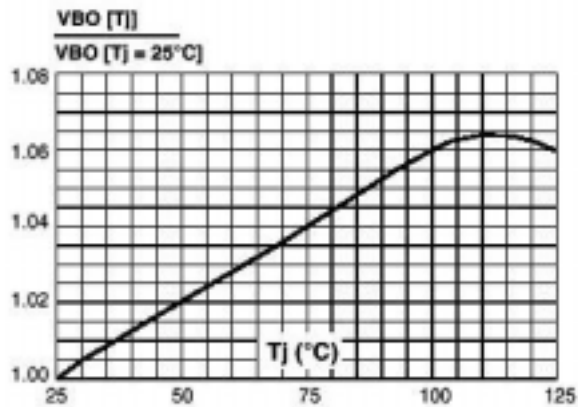


Fig. 2: Repetitive peak pulse current versus pulse duration (maximum values).

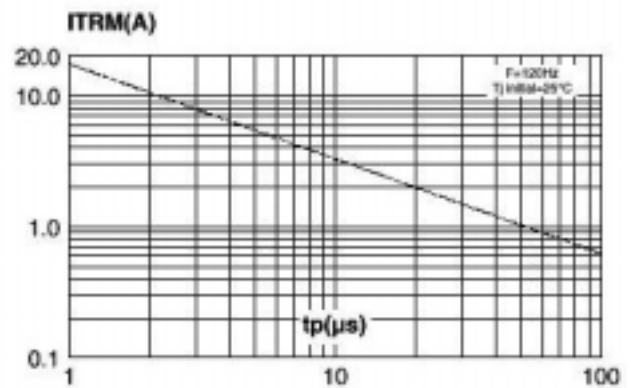


Fig. 3: Time duration while current pulse is higher 50mA versus C and Rs (typical values).

